2SK2380

Silicon N-Channel Junction FET

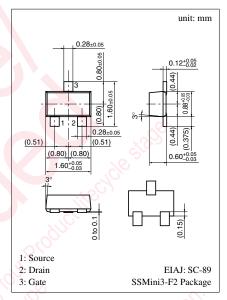
For impedance conversion in low frequency For infrared sensor

■ Features

- Low gate to source leakage current, I_{GSS}
- Small capacitance of C_{iss}, C_{oss}, C_{rss}
- SS-mini type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit	
Gate to Drain voltage	V_{GDO}	-40	V	
Gate to Source voltage	V _{GSO}	-40	V	
Drain current	I_{D}	±1	mA	
Gate current	I_G	10	mA	
Allowable power dissipation	P_{D}	125	mW	
Channel temperature	T _{ch}	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C O	



Marking Symbol (Example): EB

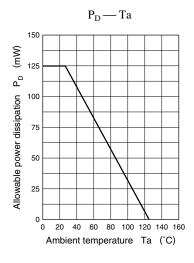
■ Electrical Characteristics (Ta = 25°C)

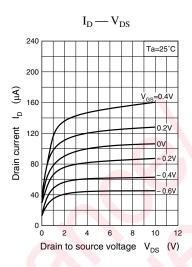
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I _{DSS} *	$V_{DS} = 10V, V_{GS} = 0$	50		200	μA
Gate to Source leakage current	I_{GSS}	$V_{GS} = -20V, V_{DS} = 0$		200	- 0.5	nA
Gate to Drain voltage	V_{DS}	$I_{G} = -10\mu A, V_{DS} = 0$	-40	7		V
Gate to Source cut-off voltage	V_{GSC}	$V_{DS} = 10V, I_D = 1\mu A$		-1.3	-3	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	0.05			mS
Input capacitance (Common Source)	C _{iss}	: 10° M:)	1		pF
Output capacitance (Common Source)	C _{oss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		0.4		pF
Reverse transfer capacitance (Common Source)	C _{rss}	coi.)		0.4		pF

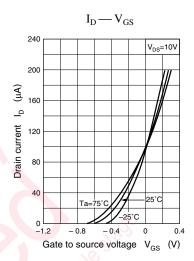
^{*} IDSS rank classification

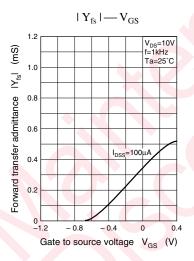
Runk	Q	R	S
I _{DSS} (mA)	50 to 100	70 to 130	100 to 200
Marking Symbol	EBQ	EBR	EBS

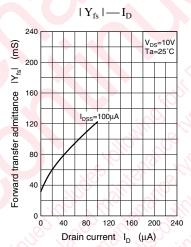
262 Panasonic

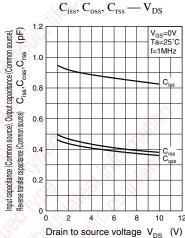












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